

Chip Silicon Rectifier

Formosa MS

FFM101-L THRU FFM107-L

Fast recovery type

Features

- Plastic package has Underwriters Laboratory Flammability Classification 94V-O Utilizing Flame Retardant Epoxy Molding Compound.
- For surface mounted applications.
- Exceeds environmental standards of ML-S-19500 / 228
- Low leakage current

Mechanical data

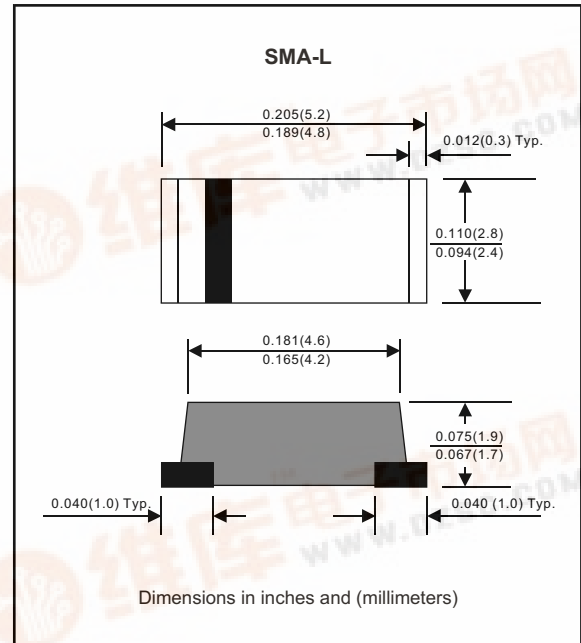
Case : Molded plastic, JEDEC DO-214AC

Terminals : Solder plated, solderable per MIL-STD-750, Method 2026

Polarity : Indicated by cathode band

Mounting Position : Any

Weight : 0.0015 ounce, 0.05 gram



MAXIMUM RATINGS (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	Symbol	MIN.	TYP.	MAX.	UNIT
Forward rectified current	Ambient temperature = 55°C	I_0			1.0	A
Forward surge current	8.3ms single half sine-wave superimposed on rate load (JEDEC methode)	I_{FSM}			30	A
Reverse current	$V_R = V_{RRM}$ $T_A = 25^{\circ}\text{C}$	I_R			5.0	μA
	$V_R = V_{RRM}$ $T_A = 100^{\circ}\text{C}$				100	μA
Thermal resistance	Junction to ambient	R_{JA}		32		$^{\circ}\text{C} / \text{W}$
Diode junction capacitance	$f=1\text{MHz}$ and applied 4vDC reverse voltage	C_J		15		pF
Storage temperature		T_{STG}	-55		+150	$^{\circ}\text{C}$

SYMBOLS	MARKING CODE	V _{RRM} ^{*1} (V)	V _{RMS} ^{*2} (V)	V _R ^{*3} (V)	V _F ^{*4} (V)	T _{RR} ^{*5} (nS)	Operating temperature (°C)
FFM101	F11	50	35	50	1.3	150	-55 to +150
FFM102	F12	100	70	100			
FFM103	F13	200	140	200			
FFM104	F14	400	280	400			
FFM105	F15	600	420	600			
FFM106	F16	800	560	800			
FFM107	F17	1000	700	1000			

*1 Repetitive peak reverse voltage

*2 RMS voltage

*3 Continuous reverse voltage

*4 Maximum forward voltage

*5 Reverse recovery time



RATING AND CHARACTERISTIC CURVES (FFM101-L THRU FFM107-L)

FIG.1-TYPICAL FORWARD CHARACTERISTICS

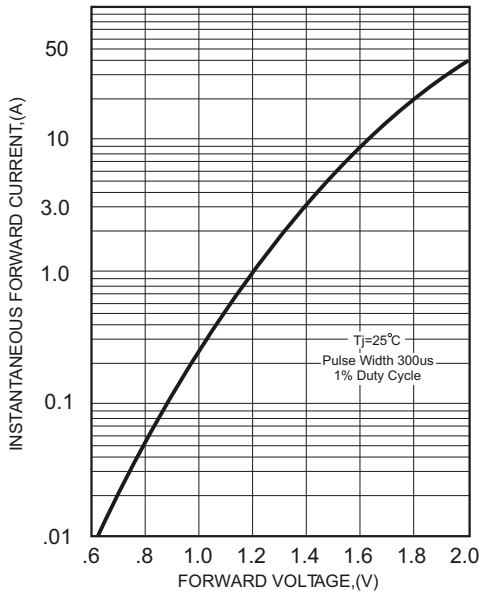


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

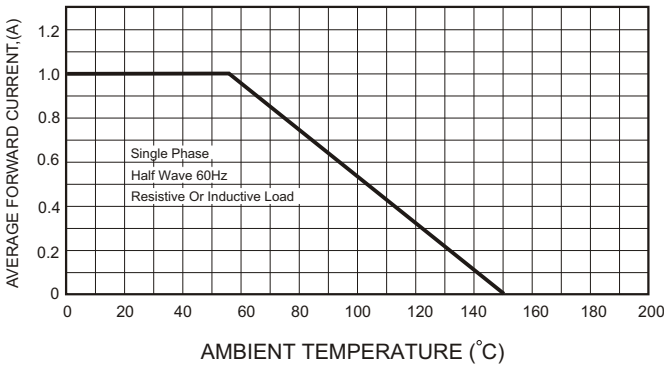


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

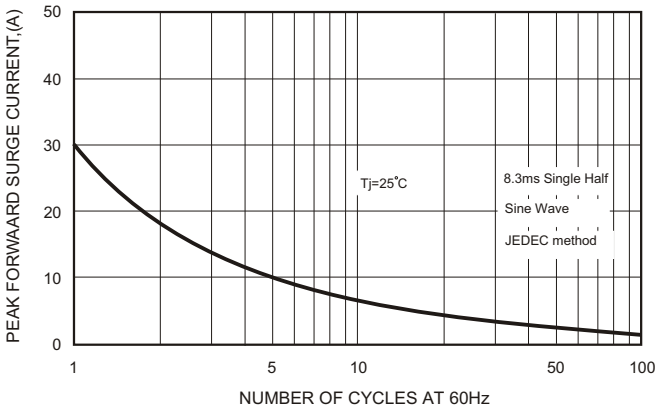
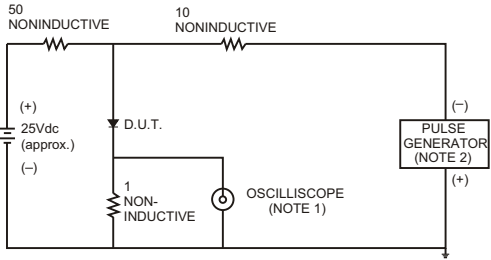


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm.22pF.
2. Rise Time= 10ns max., Source Impedance= 50 ohms.

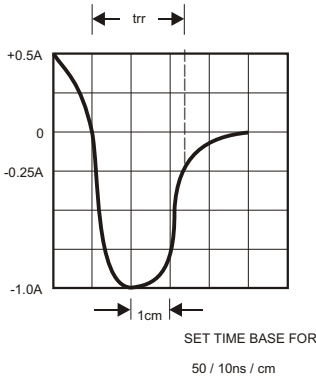


FIG.5-TYPICAL JUNCTION CAPACITANCE

